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Organized by Anodizing Research Society (ARS) of the Surface Finishing Society of Japan (SFJ).

Conference Chair: Hiroki Habazaki (Hokkaido University, Chair of ARS)
Secretary General: Shinji Yae (University of Hyogo)

Sponsored by International Society of Electrochemistry (ISE), Nanoscale | Nanoscale Advances, the Murata Science Foundation, Hitachi Metals · Materials Science Foundation, the Light Metal Educational Foundation, Inc., Hyougo Mekki Kumiai, Hyogo-ken Mekki Kenkyukai, Suga Weathering Technology Foundation, Tokyo Ohka Foundation for the Promotion of Science and Technology, Tsutomu Nakauchi Foundation, Hyogo International Association, and Okuno Chemical Industries., Co. Ltd.

Venue: Awaji Yumebutai International Conference Center, Awaji Island (Awaji-city), Hyogo, Japan.


Focus: Various aspects of anodizing science and technology

Number of participants: 130 from 15 countries (Austria, Belgium, China, Czech Republic, France, Germany, Italy, Japan, Korea, Norway, Poland, Portugal, Sweden, UK, USA)

Number of presentations: 91, 2 Plenary lectures, 7 Keynotes, 17 Invited talks, 30 Contributed oral presentations, 35 Posters.

Title of plenary lectures

Hideki Masuda (Tokyo Metropolitan University, Japan)
Fabrication of Highly Ordered Anodic Porous Alumina and Its Functional Applications

Herman Terryn (Vrije Universiteit Brussel, Belgium)
Anodized oxide films as an important interface in different aluminum applications
Best Poster Awards

(AST & Nanoscale Prizes) Growth of Anodic Nanotubular Films on Sputter-Deposited Fe-W Alloy
Laras Fadillah (Hokkaido University, Japan), Damian Kowalski, Chunyu Zhu, Yoshitaka Aoki, Hiroki Habazaki

(AST & Nanoscale Advances Prizes) Efficiency of Anodic Alumina Formation in Sulfuric Acid with Ethanol Addition
Mikimasa Matsumoto (Kogakuin University, Japan), Hideki Hashimoto, Hidetaka Asoh

(AST Prize) Low-powered Switching Characteristics of SWCNTs Transistor integrated with Al-HfZrO2 Dielectric for a Nonvolatile Memory
Seyoung Oh (Chungbuk National University, Korea), Byungjin Cho

(AST Prize) Effect of the bulk concentration of aqueous solution on ion enrichment within nanopores of porous silicon
Shota Inoguchi (Kyoto University, Japan), Kazuhiro Fukami, Atsushi Kitada, Kuniaki Murase

(AST Prize) Laser-induced breakdown spectroscopy using anodized substrates
Yusuke Shimazu (University of Hyogo, Japan), Sakiko Yoshizumi, Ayumu Matsumoto, Shinji Yae

Webpage: http://ars.sfj.or.jp/ast2019/

Photographs of the meeting
Prof. Susumu Kuwabata (Osaka University, ISE Regional Representative of Japan) gave a speech as the representative of ISE at the conference banquet.